# RT3TFFM-T150

Composite Transistor With Resistor For Switching Application Silicon Epitaxial Type

### DESCRIPTION

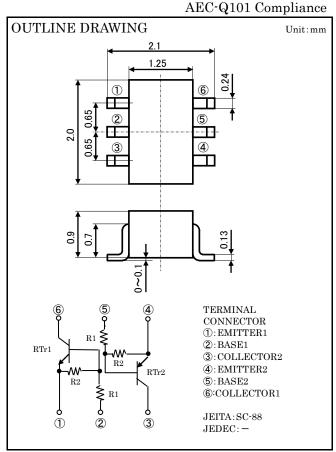
RT3TFFM is composite transistor built with RT1N431 chip and RT1P431 chip in SC-88 package.

### FEATURE

Silicon epitaxial type Each transistor elements are independent. Mini package for easy mounting

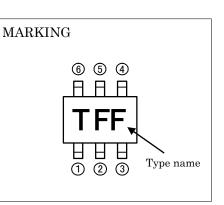
### APPLICATION

Inverted circuit, Switching circuit, Interface circuit, Driver circuit



## MAXIMUM RATING (Ta=25°C) (RTr1\_NPN, RTr2\_PNP)

SYMBOL	PARAMETER	RATING	UNIT	
VCBO	Collector to Base voltage	50	50 V	
Vebo	Emitter to Base voltage	10	V	
VCEO	Collector to Emitter voltage	50	V	
VIN	Input voltage	30	V	
IC	Collector current	100	mA	
ICM	Peak Collector current	200	mA	
$P_{T}$	Total dissipation	200	mW	
Tj	Junction temperature	+150	°C	
$T_{stg}$	Storage temperature	-55~+150	°C	



**※**PNP built in transistor of "−"sign is abbreviation.

### ELECTRICAL CHARACTERISTICS (Ta=25°C) (RTr1\_NPN, RTr2\_PNP)

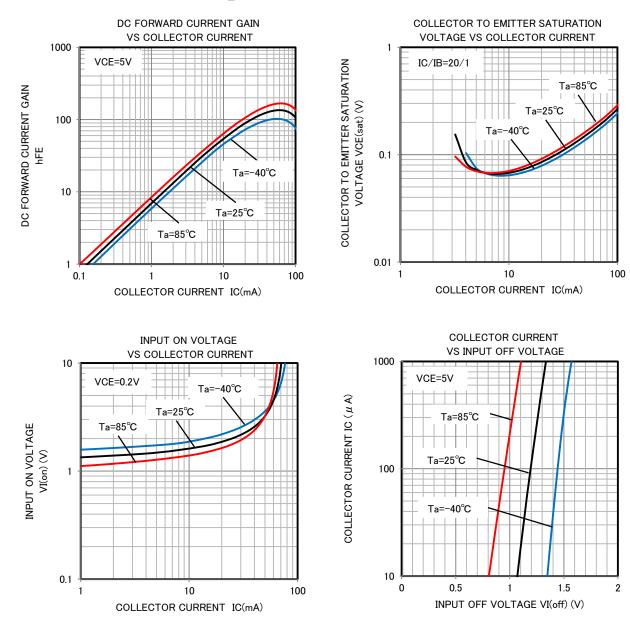
a	Parameter	Test conditions		Limits			<b>TT</b>
Symbol				Min	Тур	Max	Unit
V(BR)CEO	Collector to Emitter breakdown voltage	I <sub>C</sub> =100µА, R <sub>BE</sub> =∞		50	-	—	V
ICBO	Collector cut off current	$V_{CB}=50V$ , $I_E=0$		—	-	0.1	μA
IEBO	Emitter cut off current	$V_{EB}$ =5V, $I_C$ =0		399	532	771	μΑ
hFE	DC forward current gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA		20	-	—	-
VCE(sat)	Collector to Emitter saturation voltage	ter saturation voltage Ic=10mA, IB=0.5mA		-	-	0.3	V
VI(ON)	Input on voltage $V_{CE}$ =0.2V, I <sub>C</sub> =5mA		—	1.4	2.3	V	
VI(OFF)	Input off voltage V <sub>CE</sub> =5V, I <sub>C</sub> =100µA		0.8	1.1	—	v	
$R_1$	Input resistor	-		3.3	4.7	6.1	kΩ
$R_2/R_1$	Resistor ratio	-		0.8	1.0	1.2	—
$_{ m fr}$	Gain band width product	V <sub>CE</sub> =6V, I <sub>E</sub> =10mA	RTr1	_	200	_	MHz
			RTr2	-	150	_	

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## ISAHAYA ELECTRONICS CORPORATION

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### TYPICAL CHARACTERISTICS (RTr1\_NPN)

RT3TFFM-T150

Composite Transistor With Resistor For Switching Application Silicon Epitaxial Type

Ta=85°C

-100

Ta=25°C

40°C Ta=

-10

COLLECTOR CURRENT IC(mA)

COLLECTOR CURRENT

VS INPUT OFF VOLTAGE

-1

INPUT OFF VOLTAGE VI(off) (V)

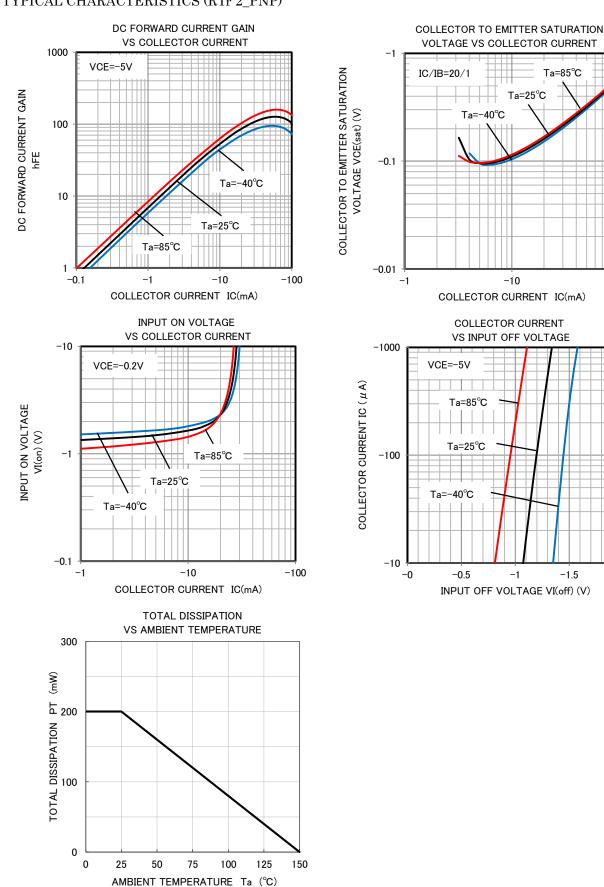
-1.5

-2

Ta=85°C

Ta=25°C

-0.5



### TYPICAL CHARACTERISTICS (RTr 2\_PNP)

### ISAHAYA ELECTRONICS CORPORATION

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